

Game Change: Monitoring Large Particles in Undiluted Slurry

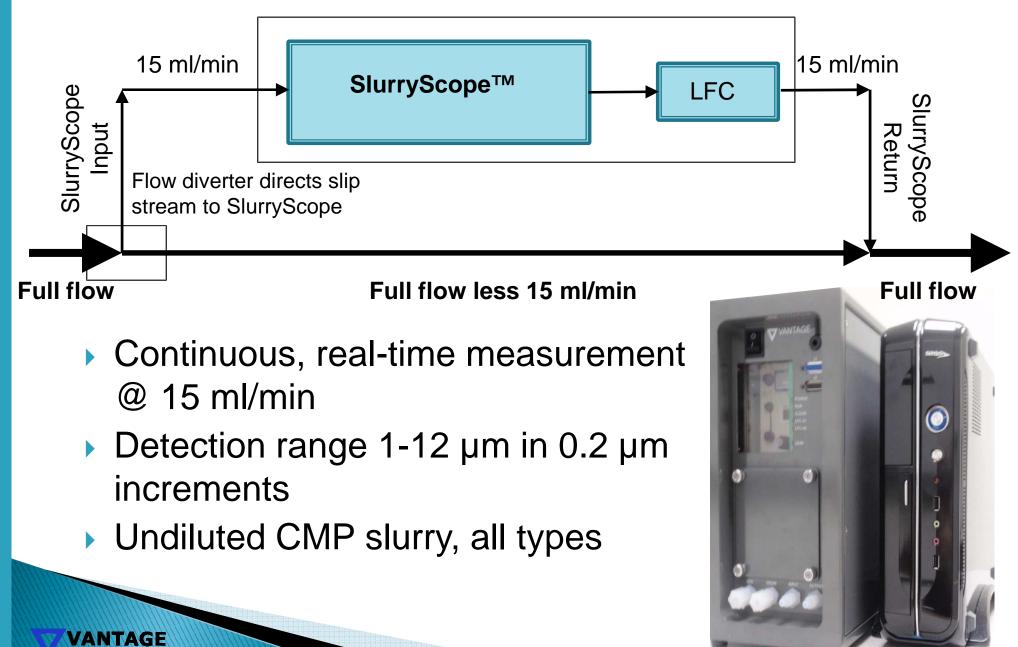
Michael A. Fury, Ph.D. Director of Market Development MFury@VantageTechCorp.com July 11, 2012



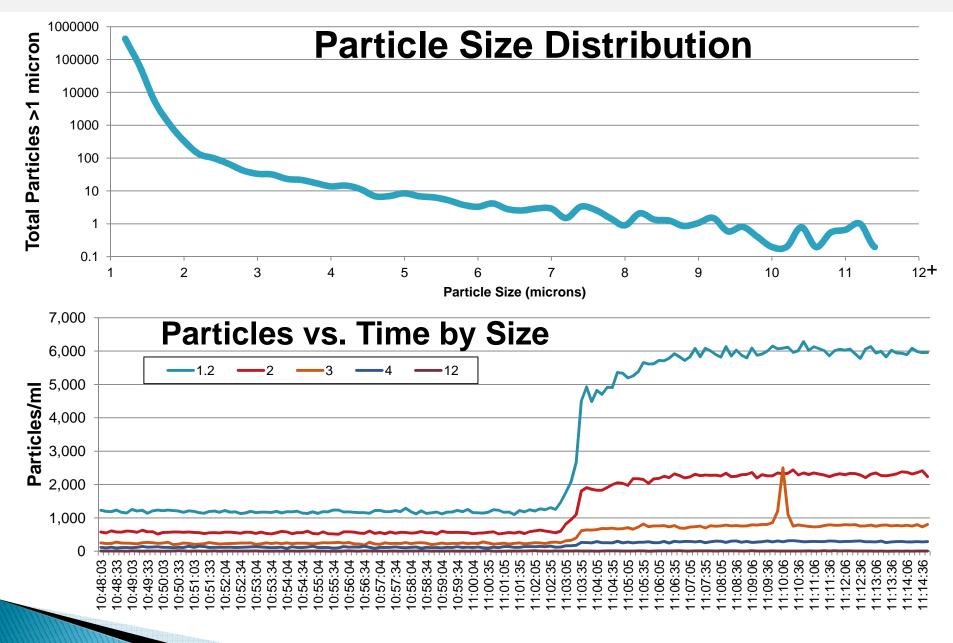
- ► Vantage SlurryScopeTM principles
- Comparison to SPOS methods
- Tales from the sub-fab
- Implications for fab operations & yield
- Conclusions



Vantage Technology SlurryScope™



SlurryScope Typical Data



Slurry Monitoring Comparison

SPOS* Methods

- Periodic sampling
- Sample size 0.25-1 ml
- Offline / near line
- Dilution to meet SPOS detector requirements

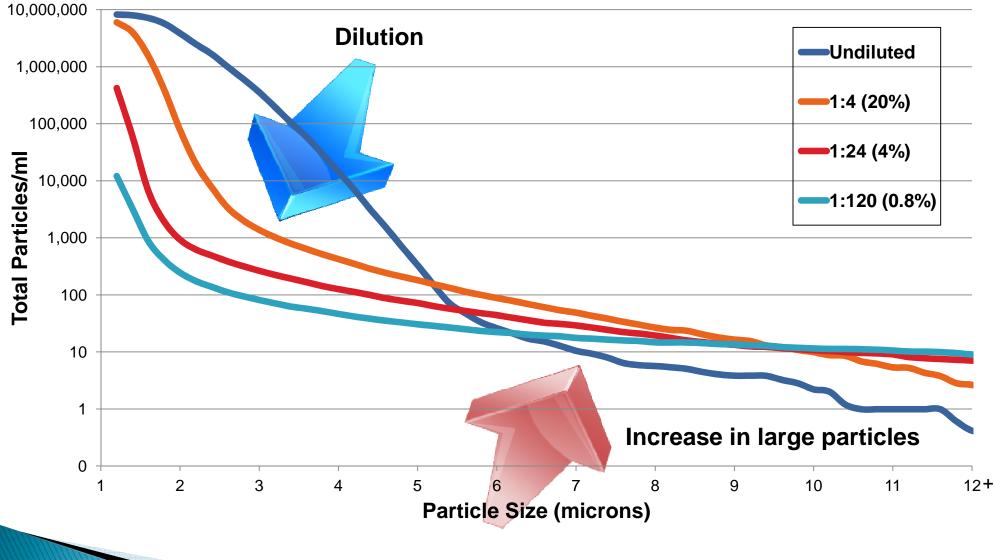
*Single Particle Optical Sizing

SlurryScope System

- Continuous monitoring
- Sampling rate 15 ml/min
- Real-time
- Undiluted at full POU concentration
- Integrates into SDS
- Integrates into polisher slurry lines at POU

SPOS: Agglomeration On Dilution

Ceria Slurry Dilution

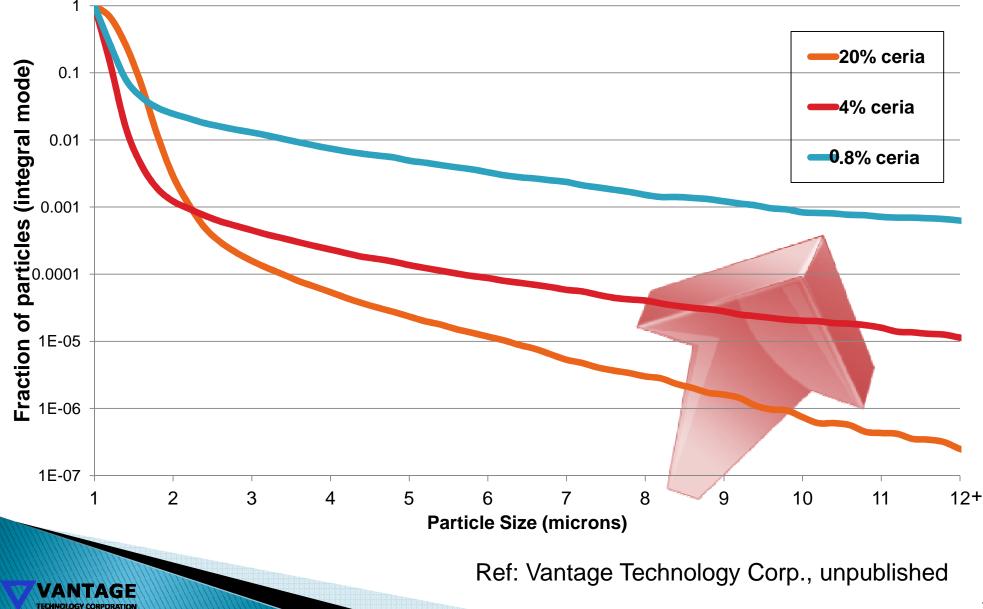


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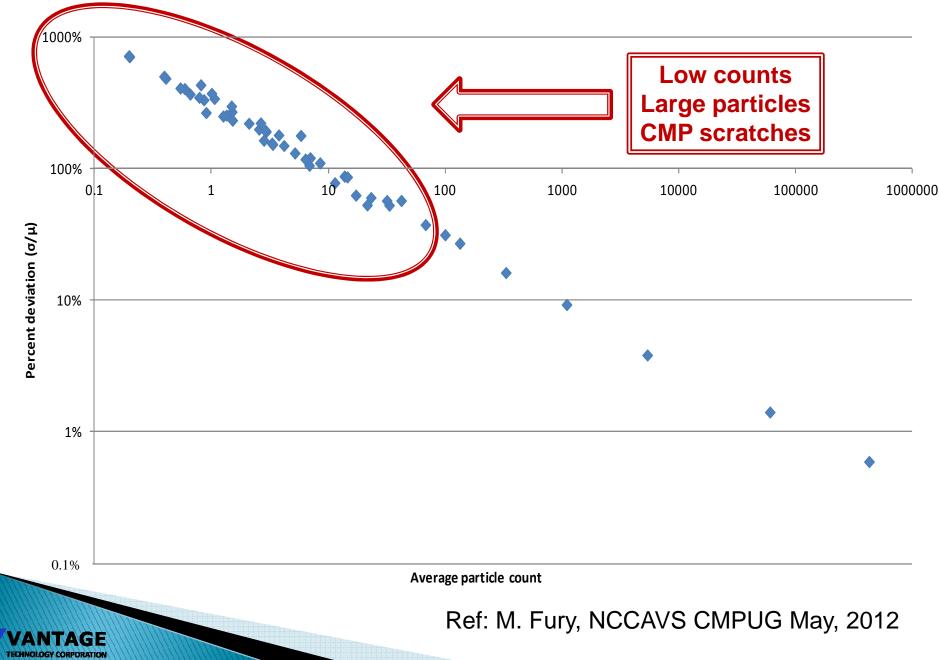
Ref: Vantage Technology Corp., unpublished

SPOS: Agglomeration On Dilution

Normalized Ceria Slurry Dilution



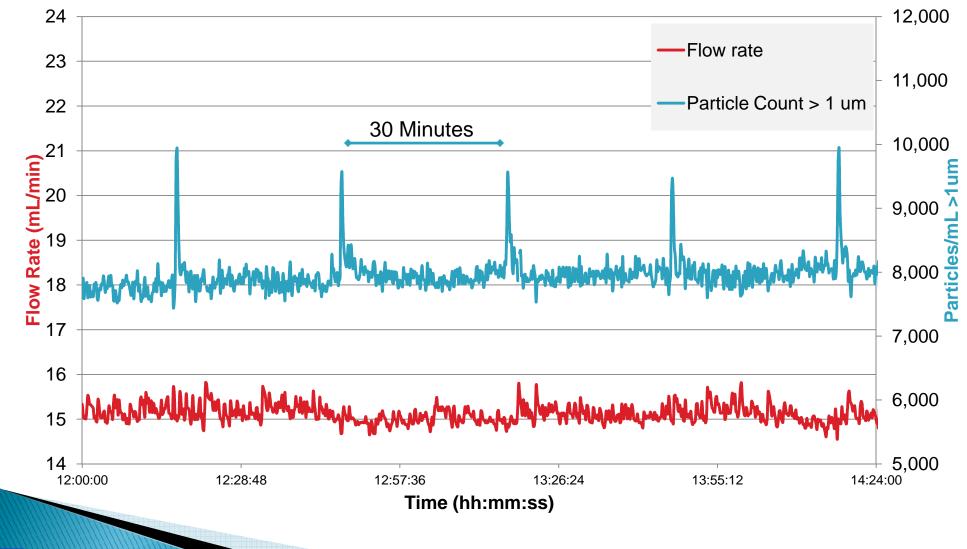
SPOS Sample Size: Percent Deviation vs. Particle Count



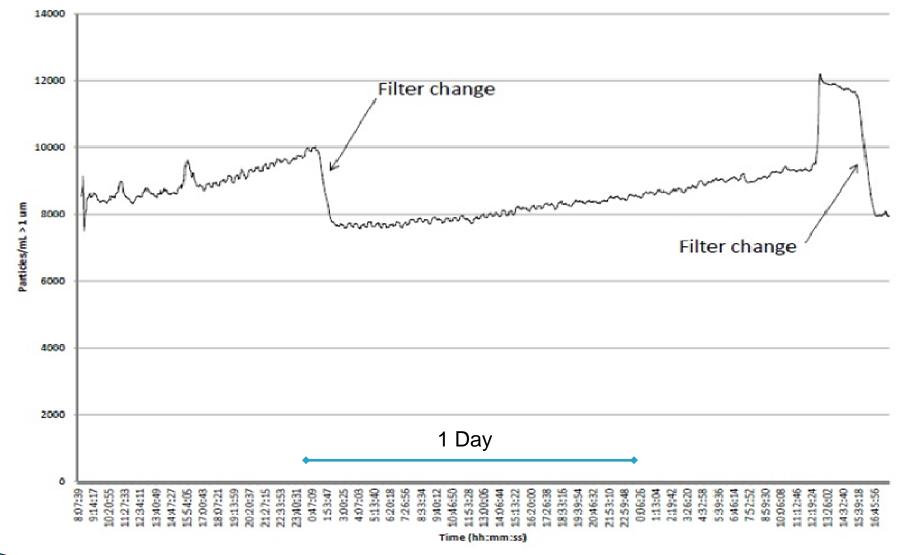
- Several examples of live sub-fab data taken from SlurryScope qualifications
- Both silica & ceria slurries are represented
- No simulations, no staged events, no chicanery of any kind
- Wafers were probably harmed during the making of this data set
- What's going on in your slurry?



Spikes in particle counts every 30 minutes while flow rate remains constant

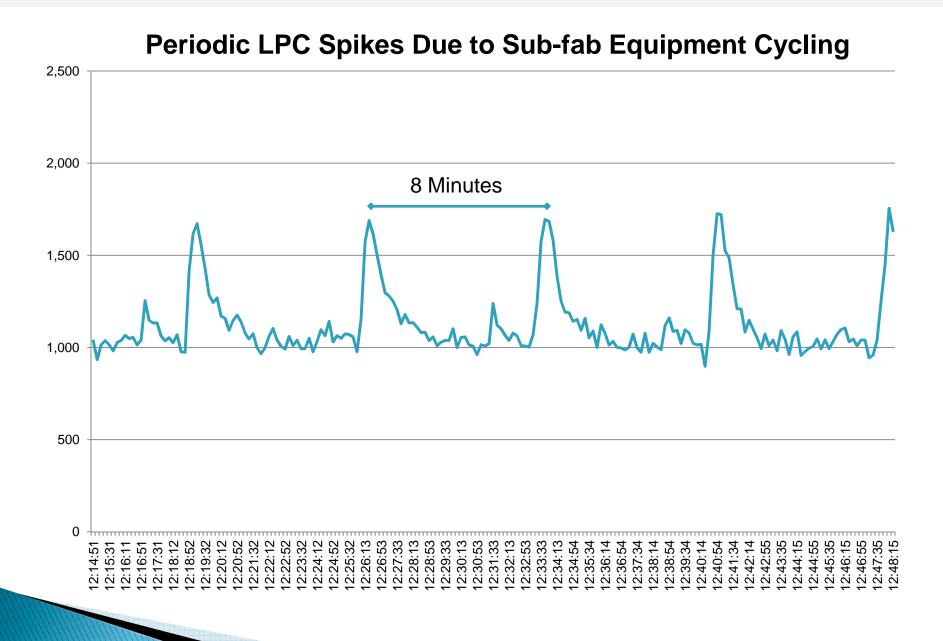


LPC Shifts Due to Filter Changes

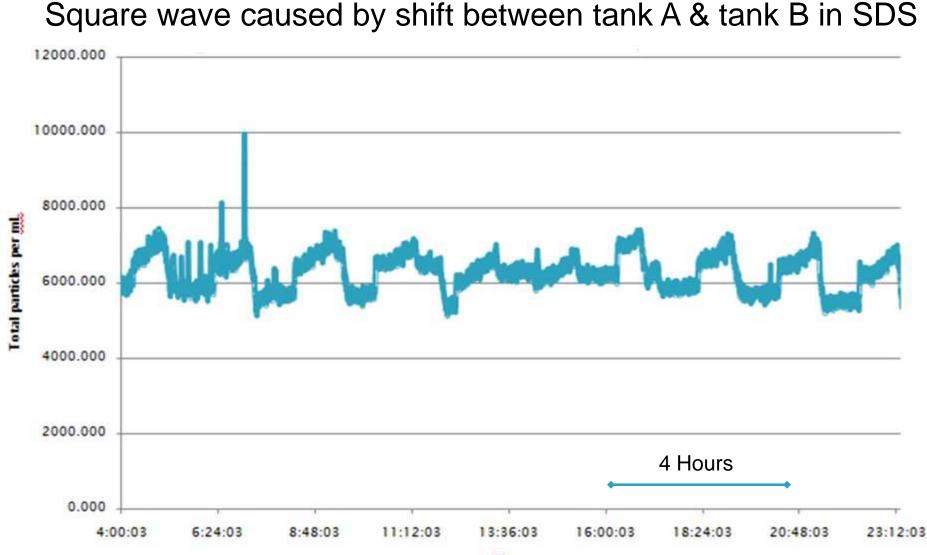


Ref: ASMC May, 2012; A. Kim, Mega Fluid Systems & M. Parkin, Vantage Technology Corp.





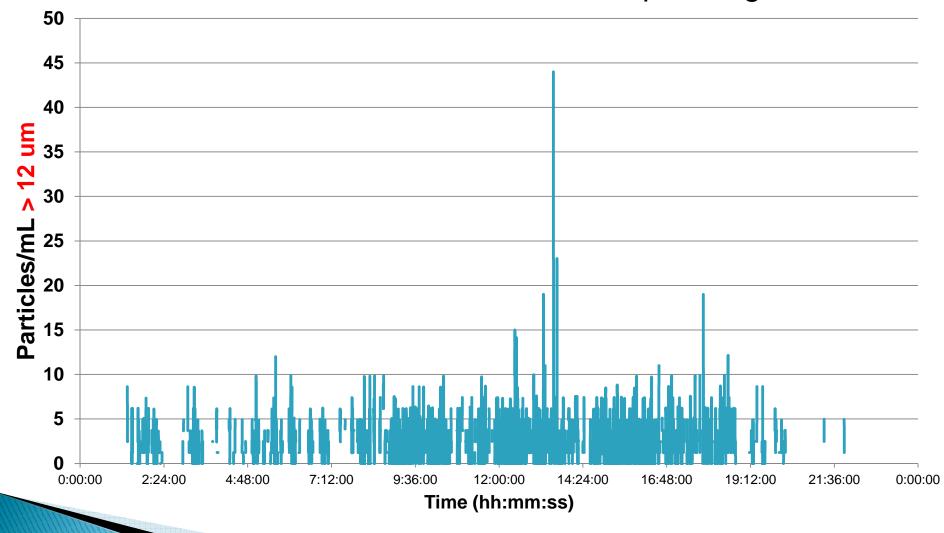




Time

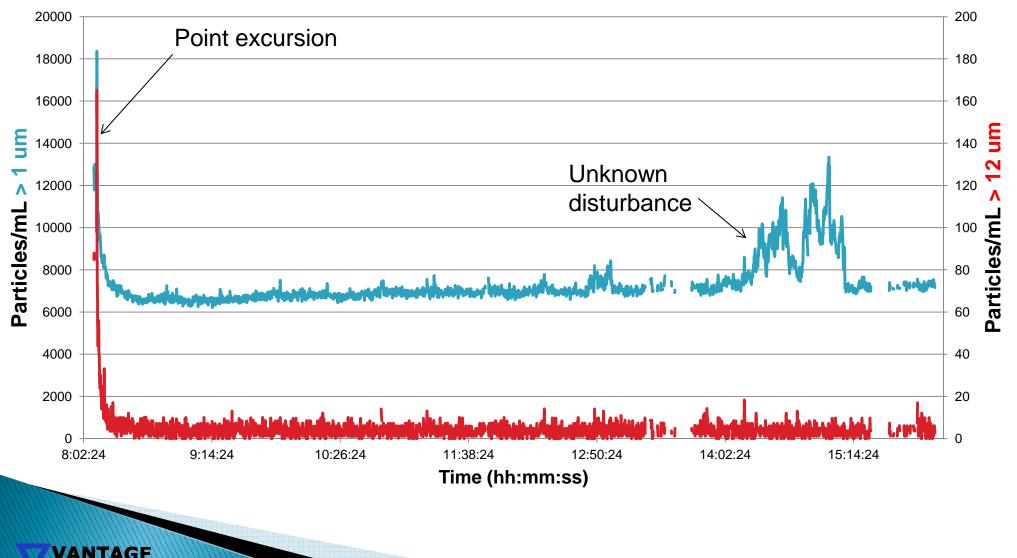


Point excursion observed in >12µm range with no evidence of same in 1-12µm range



- Point excursion observed across full size range (typical)
- Unknown LPC excursion at small particles only

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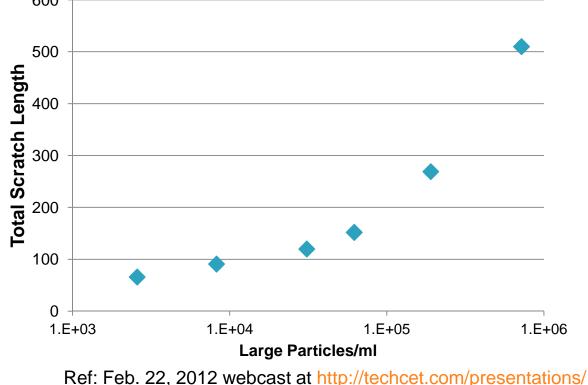


Implications for Fab Operations

- Periodic slurry monitoring can assist post-mortem diagnosis of wafer scratching
 - Cannot prevent wafer scratching from occurring
 - Low probability of capturing brief LPC excursions
 - Low probability of capturing LPC periodicity
- Continuous online slurry monitoring can identify patterns and practices that contribute to LPC excursions
 - Identify and eliminate root causes of LPC shifts
 - Reduce the incidence of slurry-induced wafer scratching
 - Applies 6σ principles to prevent wafer scratching

Implications for Fab Yield

- Vantage / Ebara experimental data shows a quantitative relationship between LPC and wafer scratches
- Customer feedback corroborates quantitative correlation across a variety of fab conditions and slurry types





Conclusions

- Periodic sampling does not reflect the dynamic behavior – and misbehavior – of slurry systems in a fab environment
- Continuous monitoring of undiluted slurry provides *new information* that allows LPC sources to be traced and eliminated, bringing CMP in line with 6σ process defect control principles
- You won't know what's happening in your slurry line until you look...



Additional Information

- Semicon West 2012: Malema Booth 625
- Semicon West 2012: Levitronix Booth 1440
- NCCAVS CMPUG May, 2012; M. Fury
- ASMC May, 2012; A. Kim, Mega Fluid Systems & M. Parkin, Vantage Technology Corp.
- Feb 22 2012 webcast: <u>http://Techcet.com/presentations/</u>
- ICPT 2011
- Solid State Technology, July 2011

http://www.VantageTechCorp.com/

